

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) An integrated circuit comprising:
a semiconductor substrate;
an epitaxial layer coupled to the substrate, the epitaxial layer having been coupled to the substrate via a transfer process comprising:
doping the epitaxial layer with a first quantity of a first ionic material and a second quantity of a second ionic material;
annealing the epitaxial layer and semiconductor substrate at a first annealing temperature, wherein the first annealing temperature is between approximately 439C and approximately 451C.
2. (Original) The integrated circuit of claim 1 wherein the sum of the first quantity of the first ionic material and the second quantity of the second ionic material is no greater than approximately $2 \times 10^{16} \text{ cm}^{-2}$.
3. (Canceled)
4. (Original) The integrated circuit of claim 1 wherein the first annealing temperature is between approximately 419C and approximately 430C.

5. (Original) The integrated circuit of claim 4 wherein the process further comprises mechanically separating a donor wafer, comprising the epitaxial layer, from a handle wafer, comprising the semiconductor substrate.
6. (Original) The integrated circuit of claim 2 wherein the second ionic material comprises hydrogen ions to react with the epitaxial layer at an energy level of approximately 40 KeV.
7. (Original) The integrated circuit of claim 6 wherein the first ionic material comprises helium ions to react with the epitaxial layer at an energy level of approximately 50 KeV.
8. (Original) The integrated circuit of claim 7 wherein the first quantity of helium ions is approximately $1 \times 10^{16} \text{ cm}^{-2}$ and the second quantity of hydrogen ions is approximately $1 \times 10^{16} \text{ cm}^{-2}$.
- 9.-35. (Canceled)